FIG. 1

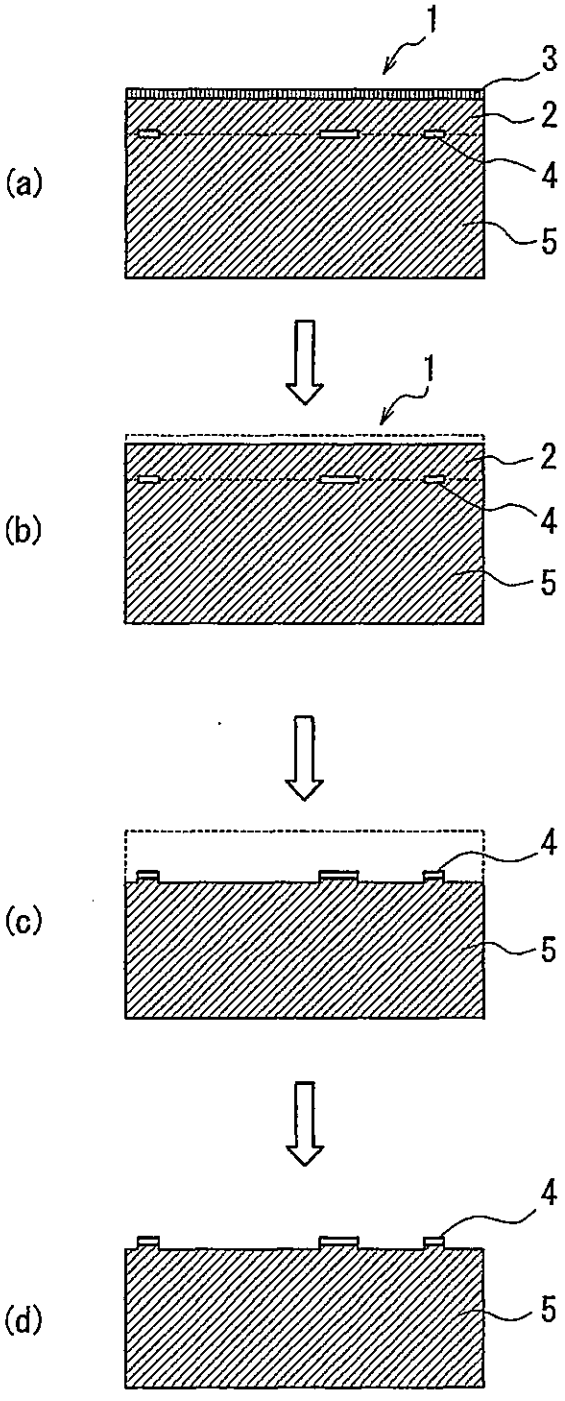


FIG. 2

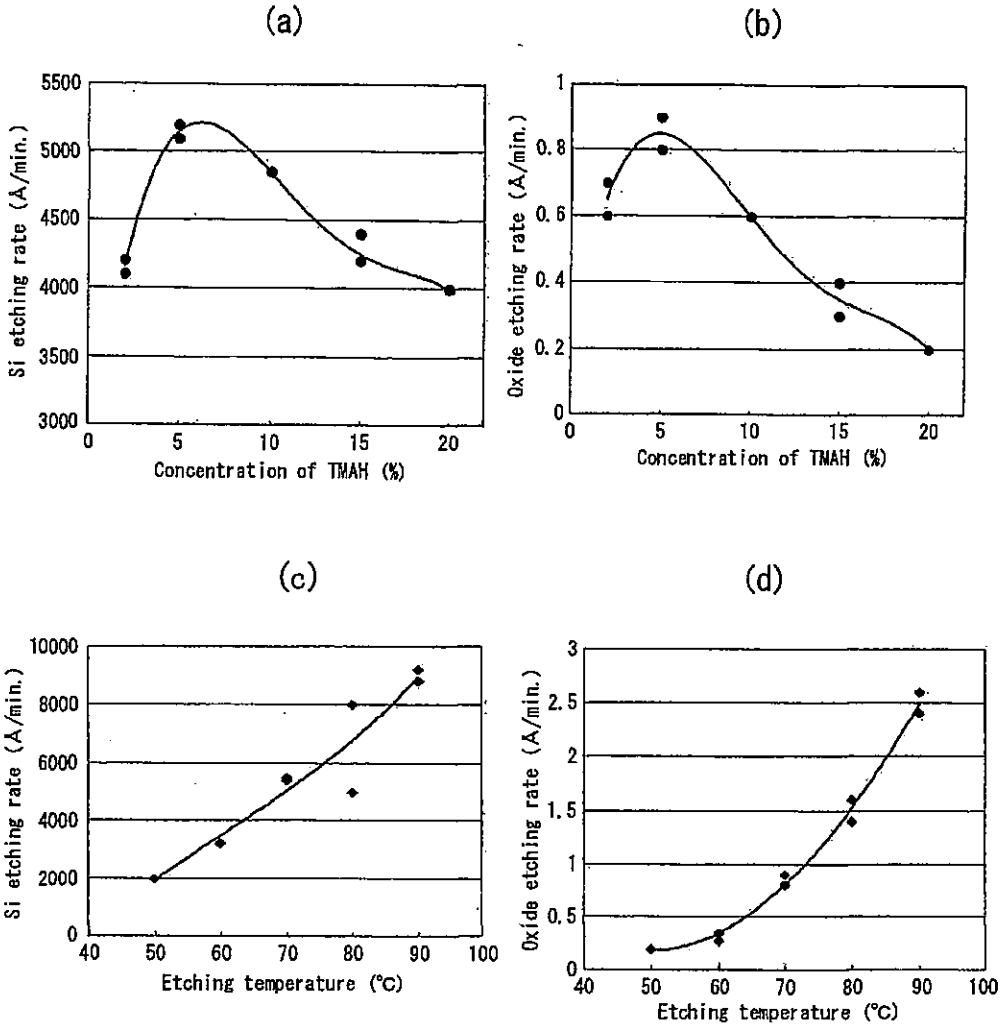

(a)
Si etching rate (A/min.)
5500
5000
4500
4000
3500
3000
0
5
10
15
20
Concentration of TMAH (%)
(b)
Oxide etching rate (A/min.)
1
0.8
0.6
0.4
0.2
0
0
5
10
15
20
Concentration of TMAH (%)
(c)
Si etching rate (A/min.)
10000
8000
6000
4000
2000
0
40
50
60
70
80
90
100
Etching temperature (°C)
(d)
Oxide etching rate (A/min.)
3
2.5
2
1.5
1
0.5
0
40
50
60
70
80
90
100
Etching temperature (°C)

FIG. 3

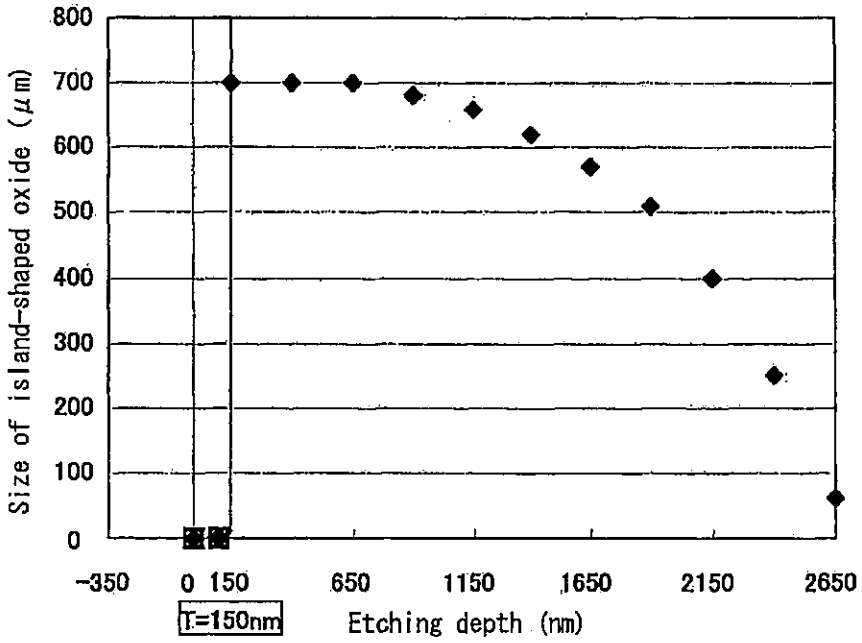

800
700
600
500
400
300
200
100
0
Size of island-shaped oxide (μm)
-350
0
150
650
1150
1650
2150
2650
T=150nm
Etching depth (nm)

FIG. 4

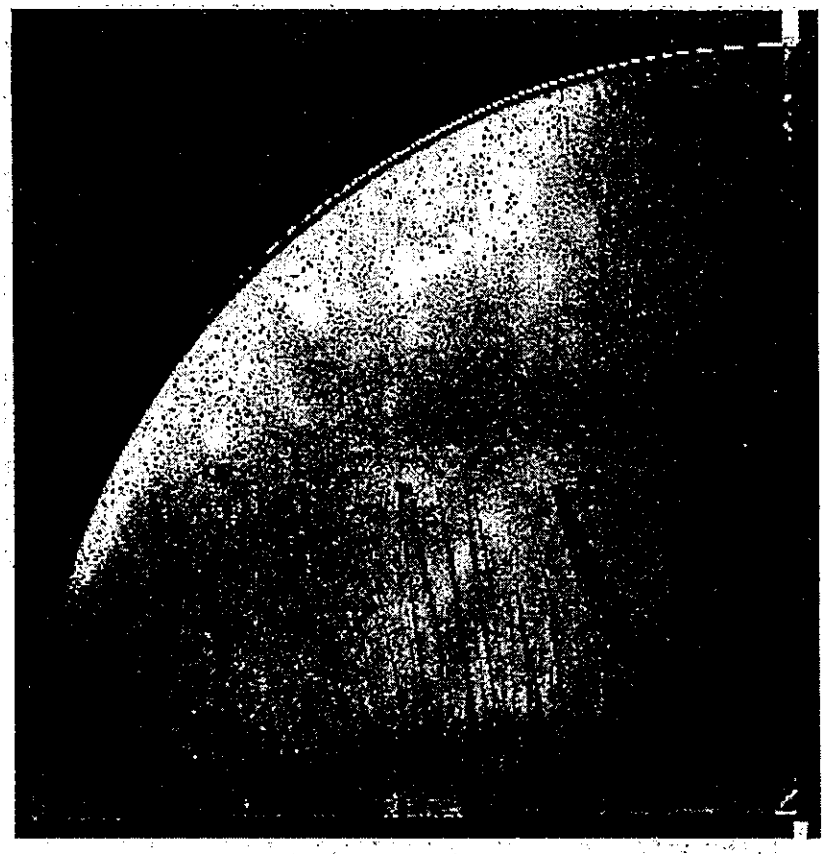


FIG. 5

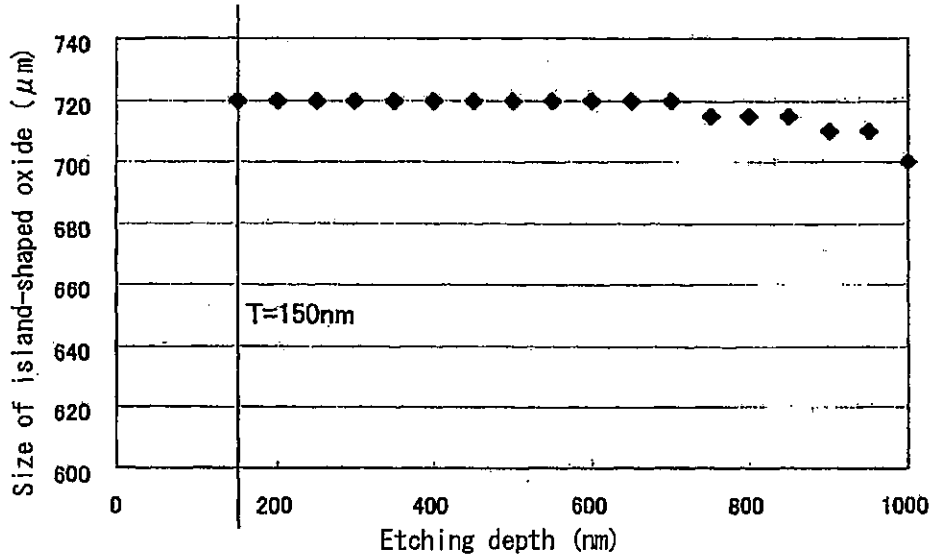
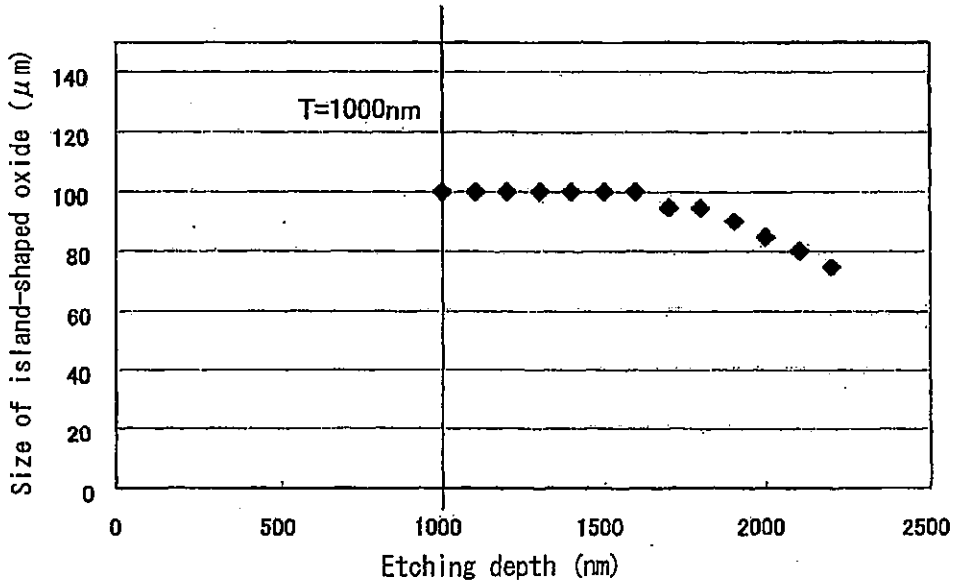

Size of island-shaped oxide (μm)
740
720
700
680
660
640
620
600
T=150nm
0
200
400
600
800
1000
Etching depth (nm)

FIG. 6


Size of island-shaped oxide (μm)
140
120
100
80
60
40
20
0
T=1000nm
0
500
1000
1500
2000
2500
Etching depth (nm)